

ABSTRACT

A field effect transistor formed on a SOI substrate is equipped with a gate (102) formed on a substrate, a source (103) and a drain (104) each spaced a specified distance from a crystal region below the gate, a first extension region (110) that extends in a channel formed between the source and an area below the gate, and a second extension region (111) that extends in a channel formed between the drain and an area below the gate, wherein junction depths (X_s , X_d) of the first and second extension regions is formed shallower than junction depths (X_t) of the source region (103) and the drain region (104).